

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claims 1-18 (cancelled)

19. (Previously presented) A method for enhancing a polysilicon to oxide selectivity during an etching process, comprising:

providing a substrate to be plasma etched in a chamber;

striking a plasma in the chamber;

flowing a silicon containing gas into the chamber while performing an over etch step of the etching process, wherein the silicon containing gas is selected from the group consisting of SiH_3CH_3 , $\text{SiH}(\text{CH}_3)_3$, SiHCl_3 , and Tetraethyl orthosilicate (TEOS); and

depositing a layer of a silicon containing oxide over a gate oxide as the substrate is being etched.

20. (Cancelled)

21. (Previously Presented) The method of claim 19, wherein the method operation of depositing a layer of a silicon containing oxide over a gate oxide as the substrate is being etched occurs during an over etch step of the etching process.

22. (Previously Presented) The method of claim 19, wherein the method operation of depositing a layer of a silicon containing oxide over a gate oxide as the substrate is being etched causes a polysilicon to oxide selectivity to increase so as to prevent any etching of the gate oxide.

Claims 23-30 are cancelled